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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Complete if Known			
		Application Number	10/654,790		
		Filing Date	9/4/03		
		First Named Inventor	Pan		
		Art Unit	2818		
		Examiner Name	M. Tran		
Sheet	1	of	5	Attorney Docket Number	

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
MH	1	J.L. PAN, J.E. McMANUS, L. GROBER and J.M. WOODWALL, Gallium-arsenide deep-level pin tunnel diode with very negative conductance, Electronics Letters, Sept. 18, 2003, Vol. 39 No. 19	
	2	JANET L. PAN, JOSEPH E.MCMANIS, THOMAS OSADCHY, LOUISE GROBER, JERRY M. WOODALL and PETER J. KINDLMANN, Gallium arsenide deep-level optical emitter for fibre optics, Nature Materials, June 2003, pp. 375-378, © 2003 Nature Publishing Group	
	3	JANET L. PAN, J.E. McMANIS, L. GROBER, J.M. WOODALL, Gallium-arsenide deep-level tunnel diode with record negative conductance and record peak current density, Solid-State Electronics 48, (2004), pp. 2067-2070, © 2004 Elsevier Ltd.	
	4	JANET L. PAN, Analytical method for finding the general optical properties of semiconductor deep centers, Journal of Applied Physics, Nov. 15, 2002, pp. 5991-6004, Volume 92, Number 10, © 2002 American Institute of Physics	
	5	JANET L. PAN, Optical emission from bound states of semiconductor deep-centers, Optics Express, Dec. 17, 2001, pp. 796-801, Vol. 9, No. 13, © 2001 OSA	
	6	S. FUKUSHIMA, K. MUKAI, N. OTSUKA, X-ray diffraction analysis of LT-GaAs's multilayer structures, Journal of Crystal Growth, 2002, pp. 1-5, © 2002 Published by Elsevier Science B.V.	
	7	G. M. MARTIN, M. L. VERHEIJKE and J.A.J. JANSEN, Measurement of the chromium concentration in semi-insulating GaAs using optical absorption, J. Appl. Phys. 50(1), Jan. 1979, pp. 467-471, © 1979 American Institute of Physics	
	8	J. SERRANO, A. WYSMOLEK, T. RUF, M. CARDONA, Spin-orbit splitting of acceptor states in Si and C, Physica B. 273-641 (1999), pp. 640-643, © 1999 Elsevier Science B.V.	
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STATEMENT BY APPLICANT**

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<i>MA</i>	11	PETER C. SERCEL, AL. L. EFROS and M. ROSEN, Intrinsic Gap States in Semiconductor Nanocrystals, Physical Review Letters, Sept. 20, 1999, pp. 2394-2397, Volume 83, Number 12, © 1999 The American Physical Society	
	12	D.T.J. HURLE, Charged native point defects in GaAs and other III-V compounds, Journal of Crystal Growth, pp. 1-7, 2002 Published by Elsevier Science B.V., © 2002 Published by Elsevier Science B.V.	
	13	J.C. BOURGOIN, H. HAMMADI, M. STELLMACHER, J. NAGLE, B. GRANDIDIER, D. STIEVENARD, J.P. NYS, C. DELERUE, M. LANNOO, As antisite incorporation in epitaxial growth of GaAs, Physica B 273-274, 1999, pp. 725-728, © 1999 Elsevier Science B.V.	
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	20	T. OBATA, S. FUKUSHIMA, T. ARAYA, N. OTSUKA, Photoluminescence of nearly stoichiometric LT-GaAs and LT-GaAs/AlAs MQW, Journal of Crystal Growth 227-228 (2001), pp. 112-116, © 2001 Elsevier Science B.V.	

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MT	21	JUN-YUAN CHEN, JENN-GEE LO and LUKE SU LU, Optical Transitions via the Structure-Defect Levels Due to Lattice Vacancies in InSb, Japanese Journal of Applied Physics, June 1991, pp. 1169-1175, Vol. 30, No. 6	
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	23	M.R. MELLOCH, J.M. WOODALL, and E.S. HARMON, Low-Temperature Grown III-V Materials, Annu. Rev. Mater. Sci., 1995, 25: 547-600, 1995 by Annual Reviews Inc.	
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	26	JEROME FAIST, FEDERICO CAPASO, DEBORAH L. SIVCO, CARLO SIRTORI, ALBERT L. HUTCHINSON; ALFRED Y. CHO, Quantum Cascade Laser, Science, New Series, Apr. 22, 1994, pp. 553-556, Volume 264, Issue 5158, © 1994 American Association for the Advancement of	
	27	JEROME FAIST, FEDERICO CAPASO, CARLO SIRTORI, DEBBIE SIVCO, ALBERT L. HUTCHINSON, SUNG-NEE G. CHU and ALFRED Y. CHO, Mid-infrared field-tunable intersubband electroluminescence at room temperature by photon-assisted tunneling in couple-quantum wells, Appl. Phys. Lett. 64 (9), Feb. 28, 1994, pp. 1144-1146, © 1994 American Institute of Physics	
	28	B. GRANDIDIER, HUAJIE CHEN, and R.M. FEENSTRA; D.T. MCINTURFF; P.W. JUODAWLKIS and S.E. RALPH, Scanning tunneling microscopy and spectroscopy of arsenic antisites in low temperature grown InGaAs, Applied Physics Letters, Mar. 8, 1999, pp. 1439-1441, Volume 74, Number 10, © 1999 American Institute of Physics	
	29	R.M. FEENSTRA, J.M. WOODALL and G.D. PETIT, Observation of Bulk Defects by Scanning Tunneling Microscopy and Spectroscopy: Arsenic Antisite Defects in GaAs, Aug. 23, 1993, pp. 1176-1179, Volume 71, Number 8, © 1993 The American Physical Society	
	30	R.M. FEENSTRA, Cross-sectional scanning tunnelling microscopy of III-V semiconductor structures, Semicond. Sci. Technol. 9, 1994, pp. 2157-2168, © 1994 IOP Publishing Ltd. (Printed in UK)	

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MA	31	G.M. MARTIN, Optical assesment of the main electron trap in bulk semi-insulating GaAs, Appl. Phys. Lett. 39(9), Nov. 1, 1981, pp. 747-748, © 1981 American Institute of Physics	
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mtc	41	SOKRATES T. PANTELIDES, The electronic structure of impurities and other point defects in semiconductors, Reviews of Modern Physics, Oct. 1978, pp. 797-858, Vol. 50, No. 4, © 1978 American Physical Society	
	42	T.C.L.G. SOLLNER, E.R. BROWN, W.D. GOODHUE, and H.Q. Le, Observation of millimeter-wave oscillations from resonant tunneling diodes and some theoretical considerations of ultimate frequency limits, Appl. Phys. Lett. 50(6), Feb. 9, 1987, pp. 332-334, © 1987 American Institute of Physics	
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